

ON Semiconductor

# FPF1203 / FPF1203L / FPF1204 / FPF12045 IntelliMAX™ Ultra-Small, Slew-Rate-Controlled Load Switch

#### **Features**

- 1.2 V to 5.5 V Input Voltage Operating Range
- Typical R<sub>ON</sub>:
  - 45 mΩ at V<sub>IN</sub>=5.5 V
  - 55 mΩ at V<sub>IN</sub>=3.3 V
  - 90 mΩ at V<sub>IN</sub>=1.8 V
  - 185 mΩ at V<sub>IN</sub>=1.2 V
- Slew Rate Control with t<sub>R</sub>:
  - FPF1203/FPF1203I/FPF1204: 100 μs
  - FPF12045: 2 μs
- Output Discharge Function on FPF1204 / 45
- Low <1.5 µA Quiescent Current</p>
- ESD Protected: Above 7 kV HBM, 2 kV CDM
- GPIO / CMOS-Compatible Enable Circuitry
- 4-Bump, WLCSP 0.76 mm x 0.76 mm, 0.4 mm Pitch

## **Description**

The FPF1203 / 03L / 04 / 45 are ultra-small integrated IntelliMA X<sup>™</sup> load switches with integrated P-channel switch and analog control features. Integrated slew-rate control prevents inrush current and the resulting excessive voltage drop on the power rail. The input voltage range operates from 1.2 V to 5.5 V to provide power-disconnect capability for post-regulated power rails in portable and consumer products. The low shut-off current allows power designs to meet standby and off-power drain specifications.

The FPF120x are controlled by a logic input (ON pin) compatible with standard CMOS GPIO circuitry found on Field Programmable Gate Array (FPGA) embedded processors. The FPF120x are available in 0.76 mm x 0.76 mm 4-bump WLCSP.

## **Applications**

- Mobile Devices and Smart Phones
- Portable Media Devices
- Tablet PCs
- Advanced Notebook, UMPC, MID
- Portable Medical Devices
- GPS and Navigation Equipment

# **Ordering Information**

Part Number	Top Mark	Switch (Typical) at 3.3V <sub>IN</sub>	Output Discharge	ON Pin Activity	t <sub>R</sub>	Package
FPF1203UCX	QL	55 mΩ	NA	Active HIGH	100 μs	
FPF1203LUCX	QP	55 mΩ	NA	Active LOW	100 μs	
FPF1204UCX	QM	55 mΩ	65 Ω	Active HIGH	100 μs	i Bailip, vvaici Ecvoi ollip
FPF1204UCX-F013 (Amkor Assembly Only)	QM	55 mΩ	65 Ω	Active HIGH	100 μs	Scale Package (WLCSP), 0.76 mm x 0.76 mm, 0.4 mm Pitch
FPF1204BUCX (Backside Laminate)	QM	55 mΩ	65 Ω	Active HIGH	100 μs	10.4 mm Filon
FPF12045UCX	NC	55 mΩ	65 Ω	Active HIGH	2 μs	

# **Application Diagram**

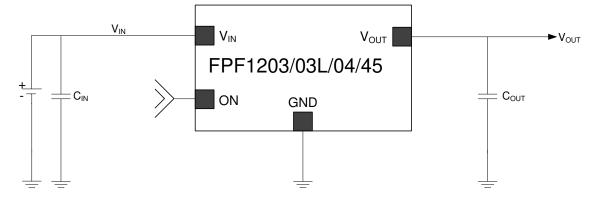


Figure 1. Typical Application

# **Functional Block Diagram**

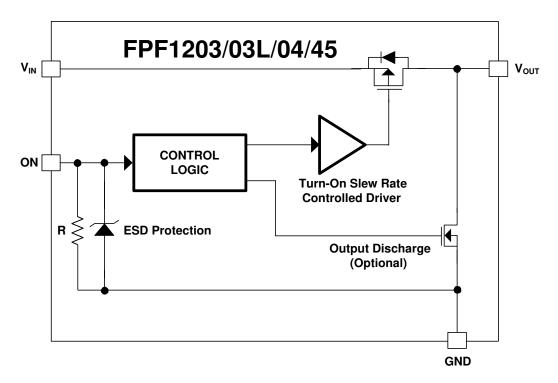


Figure 2. Functional Block Diagram (Output Discharge for FPF1204 / 45)

# **Pin Configurations**



Figure 3. WLCSP Bumps Facing Down (Top View)



Figure 4. WLCSP Bumps Facing Up (Bottom View)

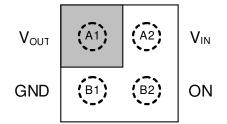


Figure 5. Pin Assignments (Top View)

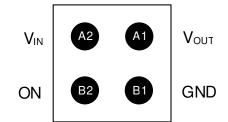


Figure 6. Pin Assignments (Bottom View)

## **Pin Definitions**

Pin #	Name	Description
A1	$V_{OUT}$	Sw itch output
A2	V <sub>IN</sub>	Supply input: input to the power switch
B1	GND	Ground
B2	ON	ON/OFF Control, active HIGH; FPF1203/04/45
B2	ON	ON/OFF Control, active LOW; FPF1203L

## **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Paramete	er	Min.	Max.	Unit
V <sub>IN</sub>	V <sub>IN</sub> , V <sub>OUT</sub> , V <sub>ON</sub> to GND		-0.3	6.0	V
Isw	Maximum Continuous Switch Current at An	nbient Operating Temperature		2.2	Α
P <sub>D</sub>	Power Dissipation at TA=25°C			1.0	W
T <sub>STG</sub>	Storage Temperature Range		-65	+150	°C
ΘJA	Thermal Resistance, Junction-to-Ambient	1S2P with One Thermal Via (1)		110	°C/W
OJA	memai resistance, unction to Ambient	1S2P without Thermal Via (2)		95	)
ESD	Electrostatic Discharge Capability (1'2)	Human Body Model, JESD22-A114	7		kV
	Local obtain Disortary Outpublinty 12	Charged Device Model, JESD22-C1 01	2		

#### Notes:

- 1. Measured using 2S2P JEDEC std. PCB.
- 2. Measured using 2S2P JEDEC PCB COLD PLATE Method.

## **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. ON Semiconductor does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Min.	Max.	Unit
V <sub>IN</sub>	Input Voltage	1.2	5.5	V
T <sub>A</sub>	Ambient Operating Temperature	-40	+85	°C

## **Electrical Characteristics**

Unless otherwise noted,  $V_{IN}$ =1.2 V to 5.5 V and  $T_A$ =-40 to +85°C. Typical values are at  $V_{IN}$ =3.3 V and  $T_A$ =25°C.

Symbol		meter	Condition	Min.	Тур.	Max.	Unit
Basic Op	eration						
V <sub>IN</sub>	Supply Voltage			1.2		5.5	V
I <sub>Q(OFF)</sub>	Off Supply	FPF1203/04/45	V <sub>ON</sub> =GND, V <sub>OUT</sub> =Open, V <sub>IN</sub> =5.5 V		0.1	1.0	μΑ
iQ(UFF)	Current	FPF1203L	V <sub>ON</sub> =V <sub>IN</sub> , V <sub>OUT</sub> =Open, V <sub>IN</sub> =5.5 V		1.0	2.0	μπ
Isp	Shutdow n	FPF1203/04/45	V <sub>ON</sub> =GND, V <sub>OUT</sub> =GND		0.1	1.0	μA
ISD	Current	FPF1203L	V <sub>ON</sub> =V <sub>IN</sub> , V <sub>OUT</sub> =GND		1.2	3.0	μΛ
lα	Quiescent	FPF1203/04/45	I <sub>OUT</sub> =0 mA, V <sub>ON=</sub> V <sub>IN</sub> , =5.5 V		0.1	1.5	μA
iQ	Current	FPF1203L	$I_{OUT}=0$ mA, $V_{ON}=GND$ , $V_{IN}=5.5$ V		0.1		μΛ
			V <sub>IN</sub> =5.5 V, l <sub>OUT</sub> =200 mA, T <sub>A</sub> =25°C		45	55 <sup>(3)</sup>	
			V <sub>IN</sub> =3.3 V, I <sub>OUT</sub> =200 mA, T <sub>A</sub> =25°C		55	65 <sup>(3)</sup>	
Ron	On Resistance		V <sub>IN</sub> =1.8 V, I <sub>OUT</sub> =200 mA, T <sub>A</sub> =25°C		90	100 <sup>(3)</sup>	mΩ
			$V_{IN}$ =1.2 V, $I_{OUT}$ =200 mA, $T_A$ =25°C		185	220 <sup>(3)</sup>	
			V <sub>IN</sub> =1.8 V, l <sub>OUT</sub> =200 mA, T <sub>A</sub> =85°C <sup>(3)</sup>			105	
R <sub>PD</sub>	Output Discharg	e Rpull down	V <sub>IN</sub> =3.3 V, V <sub>ON</sub> =OFF, I <sub>FORCE</sub> =20 mA, T <sub>A</sub> =25°C, FPF1204 / FPF12045		65	75	Ω
$V_{\text{IH}}$	On Input Logic F	HGH Voltage	V <sub>IN</sub> =1.2 V to 5.5 V	1.15			V
V <sub>IL</sub>	On Input Logic L	OW Voltage	V <sub>IN</sub> =1.2 V to 5.5 V			0.65	٧
R <sub>ON_PD</sub>	Pull-Down Resis	tance at ON Pin	V <sub>IN</sub> =1.2 V to 5.5 V		8.3		ΜΩ
lon	On Input Leakag	е	V <sub>ON</sub> =V <sub>IN</sub> or GND			1	μA
Dynamic	Characteristics						
t <sub>DON</sub>	Turn-On Delay (4	)			70		
t <sub>R</sub>	V <sub>OUT</sub> Rise Time <sup>(2</sup>	1)			100		
ton	Turn-On Time <sup>(6)</sup>		V <sub>IN</sub> =3.3 V, R <sub>L</sub> =10 Ω, C <sub>L</sub> =0.1 μF,		170		
t <sub>DON</sub>	Turn-On Delay 4	)	T <sub>A</sub> =25°C, FPF12045		2		μs
t <sub>R</sub>	V <sub>OUT</sub> Rise Time (2	1)			2		
ton	Turn-On Time <sup>(6)</sup>		1		4		
tDOFF	Turn-Off Delay (4	·'5 <sup>)</sup>			0.5		
t <sub>F</sub>	V <sub>OUT</sub> Fall Time (4)	·5 <sup>)</sup>	$V_{IN}$ =3.3 V, $R_{L}$ =10 Ω, $C_{L}$ =0.1 $\mu$ F, $T_{A}$ =25°C, FPF1203L		2.0		μs
toff	Turn-Off Time 5'	7)	1A=25 G, FFF1203L		2.5		
tDOFF	Turn-Off Delay (4	·'5 <sup>)</sup>			6	† †	
t <sub>F</sub>	V <sub>OUT</sub> Fall Time 4	·5 <sup>)</sup>	$V_{IN}$ =3.3 V, $R_L$ =500 $\Omega$ , $C_L$ =0.1 $\mu$ F, $T_A$ =25°C, FPF1203L		115	+	μs
toff	Turn-Off Time <sup>(5)</sup>	7 <sup>)</sup>	114-23 0, 111 12031		121	+	
tDOFF	Turn-Off Delay (4	·5 <sup>)</sup>			4.0	† †	
	V <sub>OUT</sub> Fall Time 4	·5 <sup>)</sup>	V <sub>IN</sub> =3.3 V, R <sub>L</sub> =10 Ω, C <sub>L</sub> =0.1 μF,		2.9	$\dagger$	μs
t <sub>F</sub>	1 00   1 011 1 11110		T <sub>A</sub> =25°C, FPF1203		7.0	+ -	•
t <sub>F</sub>	Turn-Off Time 5'	7)			7.3		
					6		
toff	Turn-Off Time (5)	·'5'	V <sub>IN</sub> =3.3 V, R <sub>L</sub> =500 Ω, C <sub>L</sub> =0.1 μF, T <sub>A</sub> =25°C, FPF1203				μs

Continued on the following page...

## **Electrical Characteristics**

Unless otherwise noted,  $V_{IN}=1.2~V$  to 5.5 V and  $T_A=-40$  to +85°C. Typical values are at  $V_{IN}=3.3~V$  and  $T_A=25$ °C.

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
tDOFF	Turn-Off Delay (4'5)	V 22V 5 42 2 2 2 4 5		4.0		
t <sub>F</sub>	V <sub>OUT</sub> Fall Time <sup>(</sup> 4'5)	$V_{IN}=3.3 \text{ V}, R_L=10 \Omega, C_L=0.1 \mu\text{F}, \\ T_A=25^{\circ}\text{C}, \text{ FPF}1204/45^{(5)}$		2.5		μs
toff	Turn-Off Time (5,7)	7, 20 0, 111 120 11 10		6.5		
tDOFF	Turn-Off Delay (4,5)			6		
tF	V <sub>OUT</sub> Fall Time <sup>(</sup> 4'5'	V <sub>IN</sub> =3.3 V, R <sub>L</sub> =500Ω, C <sub>L</sub> =0.1 μF, T <sub>A</sub> =25°C, FPF1204/45 <sup>(5)</sup>		11		μs
toff	Turn-Off Time <sup>(5,7)</sup>	·//		17		

#### Notes:

- 3. This parameter is guaranteed by design and characterization; not production tested.
- 4. t<sub>DON</sub>/t<sub>DOFF</sub>/t<sub>R</sub>/t<sub>F</sub> are defined in Figure 23.
- 5. Output discharge enabled during off-state.
- 6.  $t_{ON}=t_R+t_{DON}$ .
- 7.  $t_{OFF}=t_F+t_{DOFF}$ .

## **Typical Performance Characteristics**

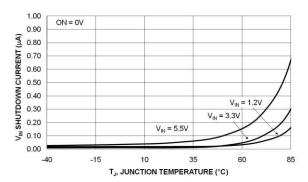


Figure 7. Shutdown Current vs. Temperature

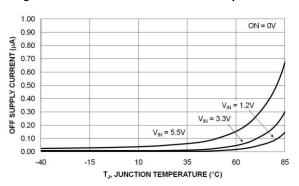


Figure 9. Off Supply Current vs. Temperature (V<sub>OUT</sub> Floating)

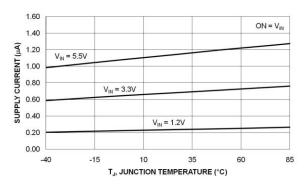


Figure 11. Quiescent Current vs. Temperature

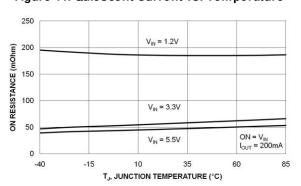


Figure 13. Ron vs. Temperature

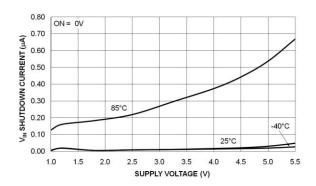


Figure 8. Shutdown Current vs. Supply Voltage

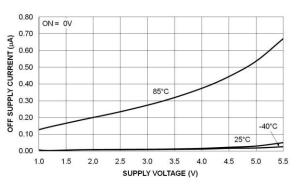


Figure 10. Off Supply Current vs. Supply Voltage  $(V_{OUT} Floating)$ 

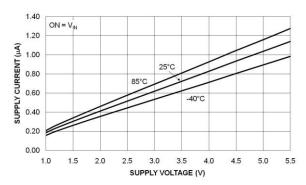


Figure 12. Quiescent Current vs. Supply Voltage

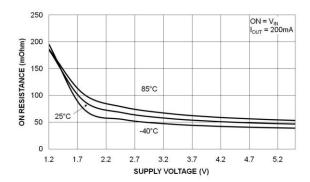
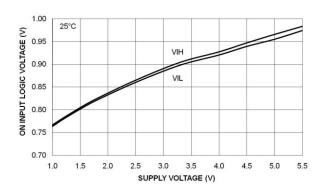


Figure 14. Ron vs. Supply Voltage

# Typical Performance Characteristics (Continued)



100

(V) 10

R<sub>DS(ON)</sub> Limit

Single Pulse

R<sub>NJA</sub> = 110°C/W

T<sub>A</sub> = 25°C

100

100ms

100ms

110ms

100ms

Figure 15. ON Pin Threshold vs.  $V_{\text{IN}}$ 

Figure 16. Drain Current vs. Drain-Source Voltage Safe Operating Area

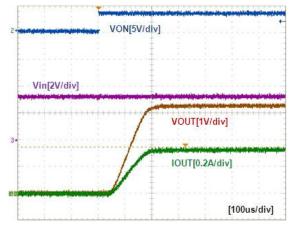


Figure 17. Turn-On Response – FPF1203 / 04 ( $V_{IN}$ =3.3 V,  $C_{IN}$ =1  $\mu$ F,  $C_{OUT}$ =0.1  $\mu$ F,  $R_L$ =10  $\Omega$ )

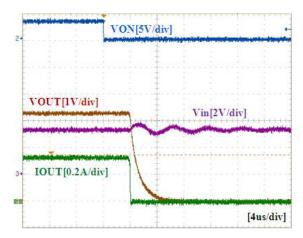


Figure 18. Turn-Off Response – FPF1203 ( $V_{IN}$ =3.3 V,  $C_{IN}$ =1  $\mu F$ ,  $C_{OUT}$ =0.1  $\mu F$ ,  $R_L$ =10  $\Omega$ )

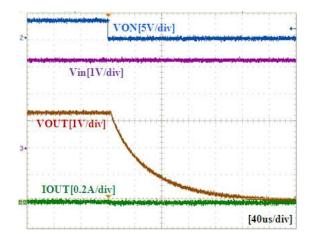
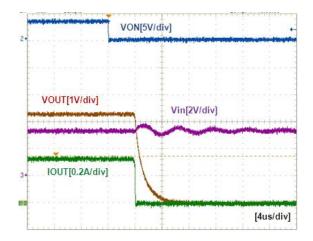
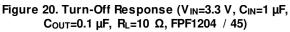


Figure 19. Turn-Off Response – FPF1203 (V  $_{IN}$  =3.3 V, C  $_{IN}$  =1  $\mu F,~C_{OUT}$  =0.1  $\mu F,~R_{L}$  =500  $~\Omega)$ 

# Typical Performance Characteristics (Continued)





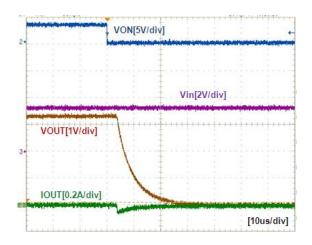


Figure 21. Turn-Off Response (V  $_{IN}$  =3.3 V, C  $_{IN}$  =1  $\mu F,$  C  $_{OUT}$  =0.1  $\mu F,$  R  $_{L}$  =500  $\Omega,$  FPF1204 / 45)

## **Operation and Application Description**

The FPF1203 / 03L / 04 / 045 are low-RoN P-channel load switches with controlled turn-on. The core of each device is a 55 m $\Omega$  P-channel MOSFET and controller capable of functioning over a wide input operating range of 1.2 to 5.5 V.

The FPF1204 / 45 contain a 65  $\Omega$  on-chip load resistor for quick output discharge when the switch is turned off.

The FPF12045 features a faster  $V_{\text{OUT}}$  Rise Time of 5  $\mu s$ .

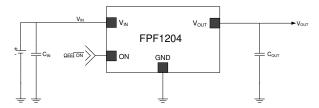


Figure 22. Typical Application

## **Input Capacitor**

To limit the voltage drop on the input supply caused by transient inrush current when the switch turns on into a discharged load capacitor or short-circuit, a capacitor must be placed between the  $V_{IN}$  and GND pins. A 1  $\mu F$  ceramic capacitor,  $C_{IN},$  placed close to the pins is usually sufficient. Higher-value  $C_{IN}$  can be used to reduce the voltage drop in higher-current applications.

## **Output Capacitor**

A 0.1  $\mu$ F capacitor,  $C_{OUT}$ , should be placed between the  $V_{OUT}$  and GND pins. This capacitor prevents parasitic board inductance from forcing  $V_{OUT}$  below GND when the switch is on.  $C_{IN}$  greater than  $C_{OUT}$  is highly recommended.  $C_{OUT}$  greater than  $C_{IN}$  can cause  $V_{OUT}$  to exceed  $V_{IN}$  when the system supply is removed. This could result in current flow through the body diode from  $V_{OUT}$  to  $V_{IN}$ .

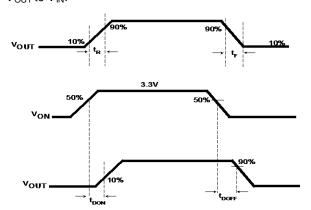


Figure 23. Timing Diagram for FPF1203/4/045

### **Board Layout**

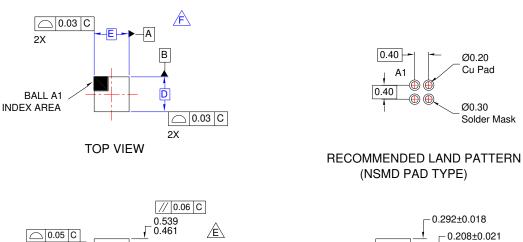
For best performance, traces should be as short as possible. To be most effective, input and output capacitors should be placed close to the device to minimize the effect of parasitic trace inductance on normal and short-circuit operation. Using wide traces or large copper planes for all pins (VIN, VOUT, ON, and GND) minimizes the parasitic electrical effects and the case-ambient thermal impedance. However, the VOUT pin should not connect directly to the battery source due to the discharge mechanism of the load switch.

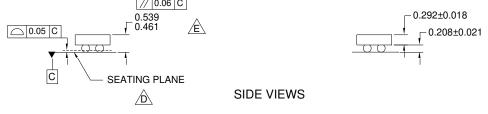
The table below pertains to the Packaging information on the following page.

#### **Product Dimensions**

D	E	X	Υ
760 μm ± 30 μm	760 μm ± 30 μm	0.180 mm± 0.018 μm	0.180 mm± 0.018 μm

# **Physical Dimensions**





## NOTES:

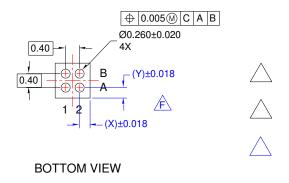


Figure 24. 4-Bump, 0.76 x 0.76 mm, Wafer-Level Chip-Scale Packaging

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